

SILICON TRANSISTOR μ PA802T

HIGH-FREQUENCY LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR (WITH BUILT-IN 2 ELEMENTS) MINI MOLD

The μ PA802T has built-in 2 low-voltage transistors which are designed to amplify low noise in the VHF band to the UHF band.

FEATURES

- Low Noise
 NF = 1.4 dB TYP. @ f = 1 GHz, VcE = 3 V, Ic = 7 mA
- High Gain
 |S_{21e}|² = 12 dB TYP. @ f = 1 GHz, VcE = 3 V, Ic = 7 mA
- · A Mini Mold Package Adopted
- Built-in 2 Transistors (2 × 2SC4227)

ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKING STYLE
μPA802T	Loose products (50 PCS)	Embossed tape 8 mm wide. Pin 6 (Q1 Base), Pin 5 (Q2 Base), Pin 4 (Q2 Emitter) face to perforation side of the tape.
μPA802T-T1	Taping products (3 KPCS/Reel)	

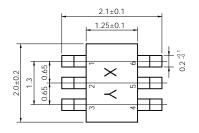
 $\begin{tabular}{ll} \textbf{Remark} & To order evaluation samples, please contact your nearby sales office. \\ & Part number for sample order: $\mu PA802T-A$ (Unit sample quantity is 50 pcs.) \\ \end{tabular}$

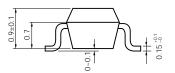
ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

PARAMETER	SYMBOL	RATING	UNIT
Collector to Base Voltage	Vсво	20	V
Collector to Emitter Voltage	Vceo	10	V
Emitter to Base Voltage	V _{EBO}	1.5	V
Collector Current	Ic	65	mA
Total Power Dissipation	Рт	150 in 1 element 200 in 2 elements ^{Note}	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65 to +150	°C

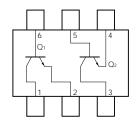
Note 110 mW must not be exceeded in 1 element.

PACKAGE DRAWINGS (Unit: mm)





PIN CONFIGURATION (Top View)



PIN CONNECTIONS

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ELECTRICAL CHARACTERISTICS (TA = 25 °C)

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	Ісво	Vcb = 10 V, IE = 0			0.8	μΑ
Emitter Cutoff Current	Ієво	V _{EB} = 1 V, I _C = 0			0.8	μΑ
DC Current Gain	hfe	$V_{CE} = 3 V$, $I_{C} = 7 \text{ mA}^{\text{Note 1}}$	70		240	
Gain Bandwidth Product	f⊤	Vce = 3 V, Ic = 7 mA, f = 1 GHz	4.5	7.0		GHz
Feed-back Capacitance	Сге	$V_{CB} = 3 V$, $I_E = 0$, $f = 1 MHz^{Note 2}$			0.9	pF
Insertion Power Gain	S ₂₁ ²	Vce = 3 V, Ic = 7 mA, f = 1 GHz	10	12		dB
Noise Figure	NF	Vce = 3 V, Ic = 7 mA, f = 1 GHz		1.4	1.7	dB
hfe Ratio	hfe1/hfe2	Vce = 3 V, lc = 7 mA A smaller value among hre of hre1 = Q1, Q2 A larger value among hre of hre2 = Q1, Q2	0.85			

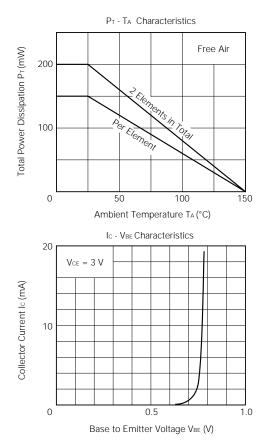
Notes 1. Pulse Measurement: $Pw \le 350 \mu s$, Duty cycle $\le 2 \%$

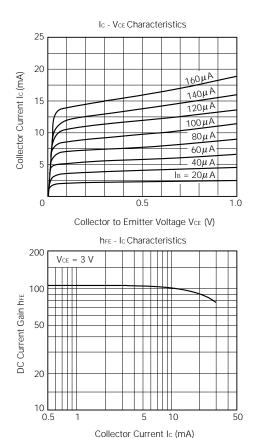
2. Measured with 3-pin bridge, emitter and case should be connected to guard pin of bridge.

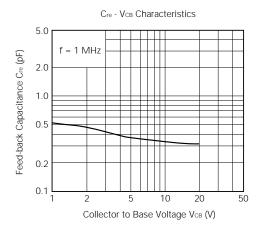
hfe CLASSIFICATION

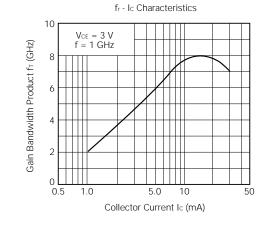
Rank	FB	GB		
Marking	R34	R35		
hre Value	70 to 150	110 to 240		

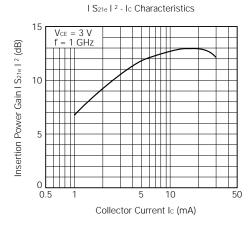
TYPICAL CHARACTERISTICS (Ta = $25 \, ^{\circ}$ C)

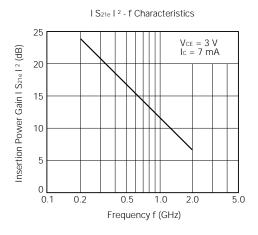


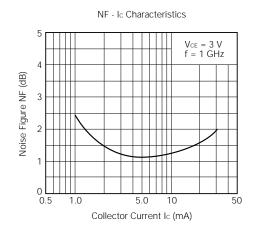












S-PARAMETERS

$V_{CF} = 3$	2 \/	Ic - :	7 m Λ	7	50.0

VCE = 3 V, IC = I	mA , Z o = !	50 12						
FREQUENCY	S	11	S	21	S	12	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.000 200.000	.804 .692	-23.8 -48.6	11.631 10.839	154.8 137.5	.023 .040	74.8 64.1	.920 .791	–16.5 –27.7
300.000	.692 .581	-48.6 -70.3	9.722	123.8	.040	64.1 59.9	.675	-27.7 -33.5
400.000	.489	-70.3 -89.0	8.519	112.9	.060	56.7	.597	-33.5 -37.0
500.000	.419	-104.9	7.434	104.1	.067	55.9	.538	-37.0 -38.7
600.000	.376	-117.1	6.468	97.5	.075	55.6	.497	-40.0
700.000	.342	-128.6	5.729	91.8	.082	55.7	.467	-41.0
800.000	.321	-138.4	5.115	86.7	.089	56.3	.443	-41.7
900.000	.305	-147.3	4.630	82.5	.096	56.1	.427	-42.5
1000.000	.296	-155.2	4.207	78.5	.104	56.4	.412	-43.6
1100.000	.289	-162.2	3.879	74.8	.111	56.0	.401	-44.6
1200.000	.284	-169.3	3.595	71.4	.119	56.4	.393	-45.8
1300.000	.282	-175.3	3.349	68.1	.127	56.2	.384	-47.3
1400.000	.281	179.0	3.133	64.8	.136	56.0	.379	-48.8
1500.000	.283	173.8	2.945	61.9	.143	55.4	.372	-50.1
1600.000	.283	168.6	2.780	58.8	.151	55.0	.367	-51.8
1700.000	.285	163.8	2.631	56.2	.160	54.4	.363	-53.7
1800.000	.286	159.9	2.514	53.3	.168	53.9	.359	-55.4
1900.000	.289	155.4	2.390	50.5	.177	53.3	.354	-57.3
2000.000	.293	151.8	2.293	47.8	.186	52.5	.351	-59.2
Vce = 3 V, Ic = 5	mA, Zo = !	50 Ω						
FREQUENCY	S	11	S	21	S	12	S2	12
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
						79.9		
100.0000 200.0000	.818 .689	-29.4 -54.3	14.580	156.2 137.5	.023		.932	-14.4 -23.4
300.0000	.594	-54.3 -73.1	12.120 10.142	124.6	.040 .052	65.1 55.0	.824 .716	-23.4 -30.3
400.0000	.500	-89.8	8.340	114.4	.063	58.5	.620	-32.2
500.0000	.457	-102.8	7.300	107.5	.069	56.4	.577	-34.2
600.0000	.404	-115.0	6.211	101.0	.081	54.9	.525	-35.1
700.0000	.377	-124.4	5.496	96.8	.084	59.5	.511	-36.1
800.0000	.359	-134.3	4.908	91.4	.091	58.4	.471	-36.2
900.0000	.342	-141.5	4.450	88.1	.097	58.4	.458	-35.3
1000.0000	.335	-150.3	4.018	84.7	.100	61.2	.440	-36.5
1100.0000	.326	-155.9	3.750	81.4	.112	61.8	.442	-36.8
1200.0000	.321	-162.4	3.410	78.1	.115	61.4	.417	-37.8
1300.0000	.317	-167.2	3.181	75.6	.124	62.3	.412	-38.5
1400.0000	.321	-173.4	2.995	72.5	.131	63.9	.411	-39.9
1500.0000	.318	-177.5	2.802	69.8	.138	63.6	.407	-40.4
1600.0000	.320	176.6	2.665	67.3	.149	66.4	.400	-41.1
1700.0000	.323	173.2	2.533	66.1	.156	65.3	.394	-43.7
1800.0000	.326	167.8	2.369	63.0	.162	65.9	.394	-44.3
1900.0000	.331	165.6	2.275	61.0	.177	65.4	.390	-45.5
2000.0000	.333	161.4	2.196	59.2	.183	64.5	.384	-47.6
$V_{CE} = 3 V, I_{C} = 3$	mA, Zo =	50 Ω						
FREQUENCY	S	511	S	21	S	12	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100.0000	.906	-22.7	9.710	161.6	.026	82.5	.962	-10.6
200.0000	.810	-43.7	8.541	145.3	.049	63.8	.895	-18.3
300.0000	.742	-60.6	7.695	133.4	.062	58.7	.811	-25.8
400.0000	.638	-76.6	6.580	122.4	.073	56.0	.732	-27.7
500.0000	.587	-89.8	5.934	114.1	.082	53.4	.680	-31.2
600.0000	.524	-102.2	5.148	107.1	.091	49.7	.624	-33.5
700.0000	.490	-111.4	4.627	102.2	.094	51.8	.603	-34.4
800.0000	.460	-121.4	4.181	96.0	.099	51.2	.568	-35.0
900.0000	.435	-129.9	3.827	92.6	.101	52.9	.540	-35.7
1000.0000	.427	-138.2	3.443	88.1	.107	50.9	.523	-36.7
1100.0000	.404	-144.9	3.199	84.2	.115	53.7	.512	-36.8
1200.0000	.399	-151.7	2.989	79.8	.113	56.6	.500	-38.6
1300.0000	.392	-157.9	2.779	77.4	.121	54.9	.489	-39.2
1400.0000 1500.0000	.392 .386	–163.6 –169.1	2.638 2.443	73.5 71.3	.126 .135	56.4 56.4	.483 .477	-40.4 -41.8
1600.0000	.386	-169.1 -174.5	2.443	71.3 68.0	.135	56.4 60.0	.477 .477	-41.8 -42.4
1700.0000	.380	-174.5 -179.7	2.344	65.3	.137	59.5	.477	-42.4 -44.4
1800.0000	.389	176.1	2.113	63.0	.151	59.4	.461	-44.4 -44.9
1900.0000	.383	172.5	2.025	61.4	.154	62.6	.456	-46.9
2000.0000	.387	168.3	1.922	58.2	.163	62.0	.464	-48.3

 V_{CE} = 3 V, I_{C} = 1 mA, Z_{O} = 50 Ω

FREQUENCY	S11		S	S21		S12		S22	
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
100.0000	1.009	-14.5	3.544	168.8	.027	78.6	.994	-5.6	
200.0000	.955	-29.7	3.359	156.3	.055	73.6	.969	-10.1	
300.0000	.937	-42.6	3.277	147.1	.073	63.4	.947	-15.9	
400.0000	.864	-56.2	3.034	136.6	.091	57.7	.898	-18.8	
500.0000	.838	-67.3	2.891	128.6	.107	51.1	.865	-22.1	
600.0000	.775	-79.3	2.674	120.0	.116	46.6	.824	-25.8	
700.0000	.745	-88.5	2.485	114.2	.125	45.2	.803	-27.5	
800.0000	.708	-99.1	2.338	106.8	.127	41.2	.776	-29.7	
900.0000	.670	-107.9	2.177	101.4	.132	40.2	.740	-31.5	
1000.0000	.649	-116.8	2.052	96.0	.135	37.2	.723	-33.7	
1100.0000	.621	-124.0	1.914	90.8	.131	36.6	.719	-34.2	
1200.0000	.608	-131.8	1.819	86.0	.129	35.4	.700	-36.3	
1300.0000	.587	-138.5	1.713	82.4	.130	35.2	.691	-37.6	
1400.0000	.587	-144.5	1.628	77.7	.128	36.1	.681	-39.2	
1500.0000	.573	-152.6	1.533	73.4	.127	36.0	.662	-40.7	
1600.0000	.559	-157.1	1.464	70.3	.124	37.5	.660	-42.7	
1700.0000	.562	-164.2	1.421	67.2	.120	39.1	.658	-44.0	
1800.0000	.557	-168.9	1.350	64.7	.122	43.3	.658	-46.0	
1900.0000	.557	-173.9	1.296	61.1	.122	45.2	.641	-47.8	
2000.0000	.551	-178.6	1.240	58.0	.124	48.5	.643	-50.1	

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